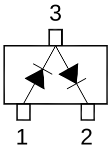
RB706F-40

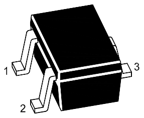
SILICON EPITAXIAL SCHOTTKY BARRIER DIODE

For low current rectification

Features

- High reliability
- Low reverse current





SOT-323 Plastic Package
Marking Code: **ZA**

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RM}	45	V
Reverse Voltage	V_R	40	V
Average Rectified Forward Current	I_O	30	mA
Peak Forward Surge Current (t = 8.3 ms)	I_{FSM}	200	mA
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	- 55 to + 125	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Typ.	Max.	Unit
Forward Voltage at I_F = 1 mA	V_F	-	-	0.37	V
Reverse Current at V_R = 10 V	I_R	-	-	1	µA
Reverse Breakdown Voltage at I_R = 10 µA	$V_{(BR)R}$	45	-	-	V
Capacitance between Terminals at V_R = 1 V, f = 1 MHz	C_T	-	2	-	pF

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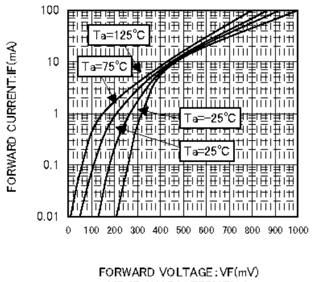
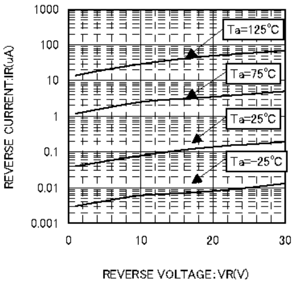
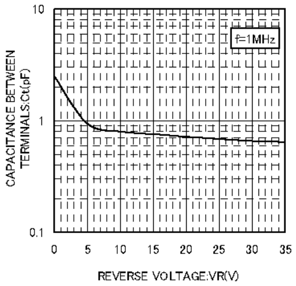


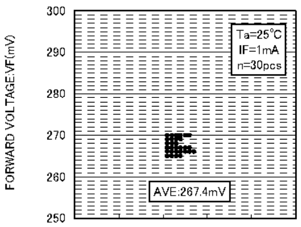
VF-IF CHARACTERISTICS



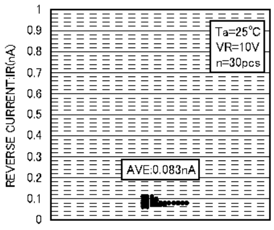
VR-IR CHARACTERISTICS



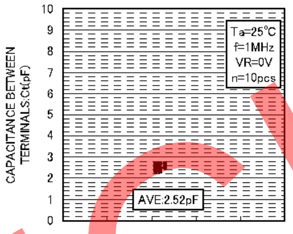
VR-Ct CHARACTERISTICS



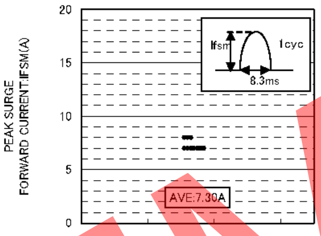
VF DIPERSION MAP



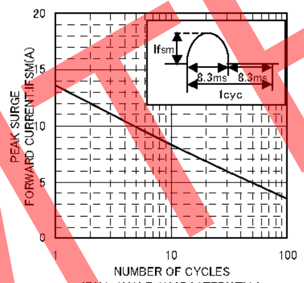
IR DISPERSION MAP



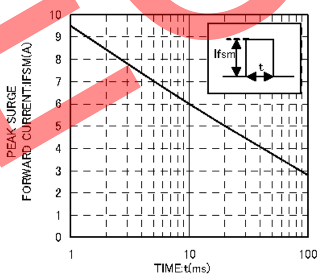
Ct DISPERSION MAP



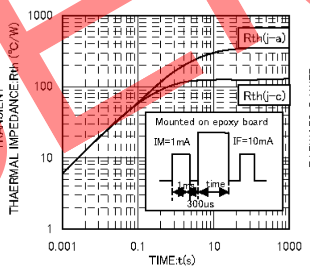
IFSM DISPERSION MAP



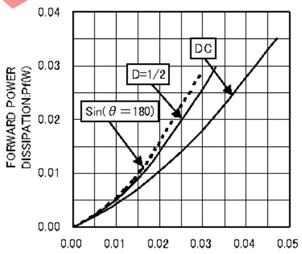
IFSM-CYCLE CHARACTERISTICS



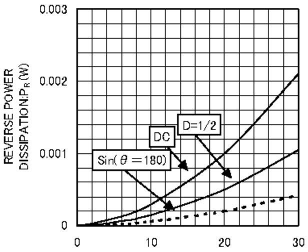
IFSM-t CHARACTERISTICS



Rth-t CHARACTERISTICS



AVERAGE RECTIFIED
FORWARD CURRENT Io(A)
Io-Pf CHARACTERISTICS



REVERSE VOLTAGE:VR(V)
VR-P_R CHARACTERISTICS